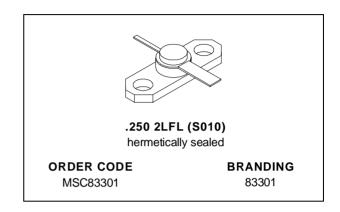


MSC83301

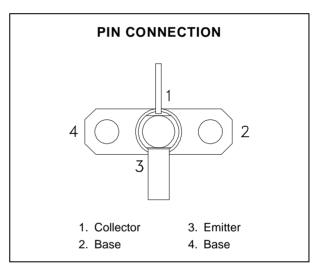
RF & MICROWAVE TRANSISTORS GENERAL PURPOSE AMPLIFIER APPLICATIONS

- REFRACTORY/GOLD METALLIZATION
- EMITTER SITE BALLASTED
- VSWR CAPABILITY ∞:1 @ RATED CONDITIONS
- HERMETIC STRIPAC® PACKAGE
- Pout = 1.0 W MIN. WITH 7.0 dB GAIN @ 3.0 GHz



DESCRIPTION

The MSC83301 is a common base hermetically sealed silicon NPN microwave power transistor utilizing an overlay, emitter site ballasted geometry with a refractory gold metallization system. This device is capable of withstanding an infinite load VSWR at any phase angle under rated conditions. The MSC83301 is designed for Class C amplifier/oscillator applications in the 1.0 - 3.0 GHz frequency range.



ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
P _{DISS}	Power Dissipation* (T _C ≤ 50°C)	6.0	W
Ic	Device Current*	200	mA
Vcc	Collector-Supply Voltage*	30	V
TJ	Junction Temperature	200	°C
T _{STG}	Storage Temperature	- 65 to +200	°C

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance*	25	°C/W

^{*}Applies only to rated RF amplifier operation

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ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

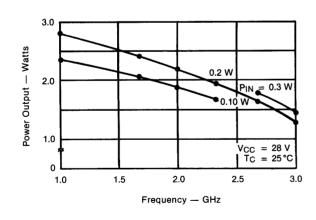
Cumah al	Took Conditions	Value			1111		
Symbol		Test Conditions		Min. Typ. Max.		Unit	
ВУсво	$I_C = 1 \text{ mA}$	$I_E = 0 \text{ mA}$		45	_	_	V
BVEBO	I _E = 1 mA	I _C = 0 mA		3.5	_	_	V
BVcer	I _C = 5 mA	$R_{BE} = 10 \Omega$		45	_	_	V
Ісво	V _{CB} = 28V			_	_	0.5	mA
hFE	V _{CE} = 5 V	I _C = 100 mA		30	_	300	_

DYNAMIC

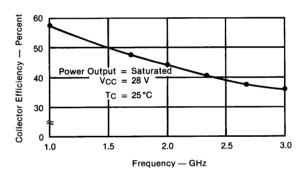
Symbol		Test Conditions		Value		Unit	
Symbol		rest Conditions	Min.	Тур.	Max.	Ullit	
Pout	f = 3.0 GHz	$P_{IN} = 0.20 \text{ W}$	$V_{CC} = 28 \text{ V}$	1.0	1.3	_	W
ης	f = 3.0 GHz	$P_{IN}=0.20\;W$	$V_{CC} = 28 \text{ V}$	33	36	_	%
P _G	f = 3.0 GHz	$P_{IN} = 0.20 \text{ W}$	V _{CC} = 28 V	7.0	8.1	_	dB
СОВ	f = 1 MHz	V _{CB} = 28 V		_	_	3.5	pF

TYPICAL PERFORMANCE

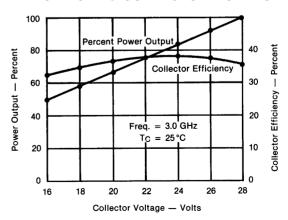
TYPICAL POWER OUTPUT vs FREQUENCY



TYPICAL COLLECTOR EFFICIENCY vs FREQUENCY



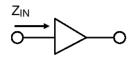
PERCENT POWER OUTPUT & COLLECTOR EFFICIENCY vs COLLECTOR VOLTAGE

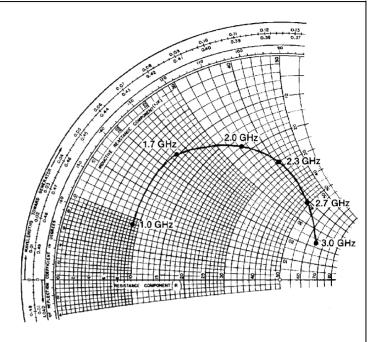


SGS-THOMSON MICROFLECTRONICS

IMPEDANCE DATA

TYPICAL INPUT IMPEDANCE

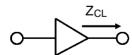


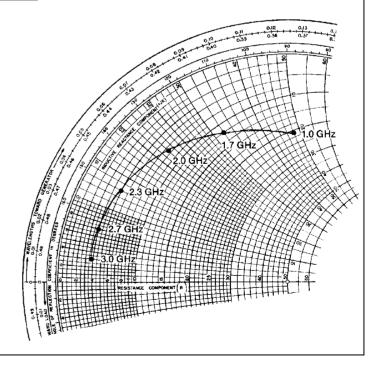


FREQ.	$Z_{IN}\left(\Omega\right)$	$Z_{CL}(\Omega)$
1.0 GHz	9.0 + j 9.0	21.0 + j 48.0
1.7 GHz	9.5 + j 23.0	12.0 + j 32.0
2.0 GHz	18.0 + j 34.5	7.5 + j 22.0
2.3 GHz	28.0 + j 41.0	5.0 + j 13.0
2.7 GHz	49.0 + j 39.0	4.0 + j 7.0
3.0 GHz	65.0 + j 22.0	3.8 + j 3.0

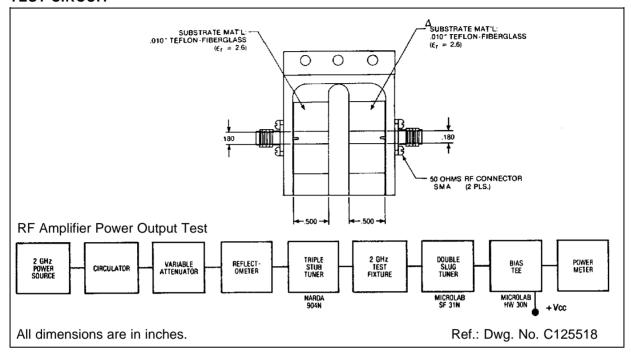
 $P_{OUT} = Saturated$ $V_{CC} = 28 V$ Normalized to 50 ohms

TYPICAL COLLECTOR LOAD IMPEDANCE

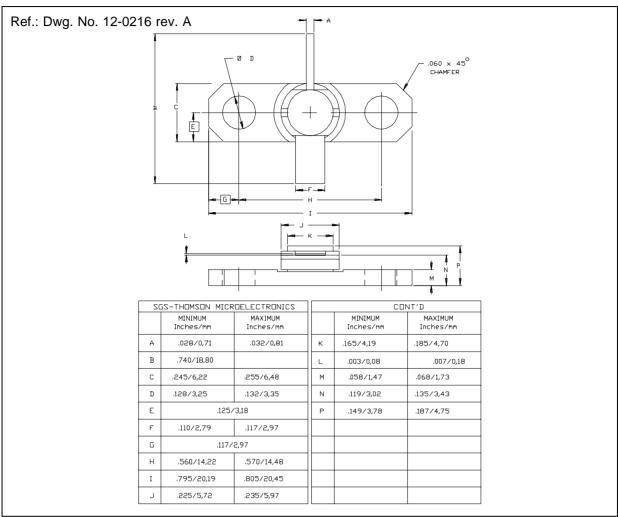




TEST CIRCUIT



PACKAGE MECHANICAL DATA



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